Taiwan Semiconductor

TAIWAN SEMICONDUCTOR

N-Channel Power MOSFET

 $600V, 9.5A, 0.38\Omega$

FEATURES

- Super-Junction technology
- High performance due to small figure-of-merit
- High ruggedness performance
- High commutation performance
- Pb-free plating
- Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21

APPLICATIONS

- Power Supply
- Lighting

TO-252 (DPAK)





ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted)					
PARAMETER		SYMBOL	IPAK/DPAK	UNIT	
Drain-Source Voltage		V _{DS}	600	V	
Gate-Source Voltage		V _{GS}	±30	V	
Continuous Drain Current (Note 1)	$T_{\rm C} = 25^{\circ}{\rm C}$		9.5	А	
	T _C = 100°C	I _D	6	А	
Pulsed Drain Current (Note 2)		I _{DM}	28.5	А	
Total Power Dissipation @ $T_c = 25^{\circ}C$	2	P _{DTOT}	83	W	
Single Pulsed Avalanche Energy (Note	e 3)	E _{AS}	64	mJ	
Single Pulsed Avalanche Current (Note 3)		I _{AS}	1.6	А	
Operating Junction and Storage Tem	nperature Range	T _J , T _{STG}	- 55 to +150	°C	

THERMAL PERFORMANCE				
PARAMETER	SYMBOL	IPAK/DPAK	UNIT	
Junction to Case Thermal Resistance	R _{eJC}	1.5	°C/W	
Junction to Ambient Thermal Resistance	$R_{\Theta J A}$	62	°C/W	

Thermal Performance Note: $R_{\Theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistances. The case-thermal reference is defined at the solder mounting surface of the drain pins. $R_{\Theta JA}$ is guaranteed by design while $R_{\Theta CA}$ is determined by the user's board design. $R_{\Theta JA}$ shown below for single device operation on FR-4 PCB in still air.

KEY PERFORMANCE PARAMETERS				
PARAMETER VALUE UNIT				
V _{DS}	600	V		
R _{DS(on)} (max)	0.38	Ω		
Qg	19.4	nC		



TSM60NB380CP



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PARAMETER	CONDITIONS	SYMBOL	MIN	ТҮР	MAX	UNIT
Static						•
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250 \mu A$	BV _{DSS}	600			V
Gate Threshold Voltage	$V_{\text{DS}} = V_{\text{GS}}, \ I_{\text{D}} = 250 \mu A$	V _{GS(TH)}	2	3	4	V
Gate Body Leakage	$V_{GS} = \pm 30 V, V_{DS} = 0 V$	I _{GSS}			±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 600V, V_{GS} = 0V$	I _{DSS}			1	μA
Drain-Source On-State Resistance (Note 4)	$V_{GS} = 10V, I_D = 2.85A$	R _{DS(on)}		0.26	0.38	Ω
Dynamic (Note 5)			<u> </u>			1
Total Gate Charge		Qg		19.4		
Gate-Source Charge	$V_{DS} = 380V, I_D = 9.5A,$ $V_{GS} = 10V$	Q _{gs}		3.5		nC
Gate-Drain Charge		Q _{gd}		8.9		
Input Capacitance	$V_{DS} = 100V, V_{GS} = 0V,$	C _{iss}		795		_
Output Capacitance	f = 1.0MHz	C _{oss}		67		pF
Gate Resistance	F = 1MHz, open drain	R _g		3.1		Ω
Switching (Note 6)						
Turn-On Delay Time		t _{d(on)}		23.6		
Turn-On Rise Time	$V_{DD} = 380V,$	t _r		11.6		
Turn-Off Delay Time	$\label{eq:rescaled_general} \begin{split} R_{\text{GEN}} &= 25\Omega, \\ I_{\text{D}} &= 9.5\text{A}, \ V_{\text{GS}} &= 10\text{V}, \end{split}$	t _{d(off)}		66		ns
Turn-Off Fall Time		t _f		9.6		
Source-Drain Diode						
Forward Voltage (Note 4)	I _S = 9.5A, V _{GS} = 0V	V _{SD}			1.4	V
Reverse Recovery Time	V _B = 100V, I _S = 9.5A	t _{rr}		272		ns
Reverse Recovery Charge	dl _F /dt = 100A/µs	Q _{rr}		2.9		μC

Notes:

1. Current limited by package.

2. Pulse width limited by the maximum junction temperature.

3. L = 50mH, I_{AS} = 1.6A, V_{DD} = 50V, R_G = 25 Ω , Starting T_J = 25 $^{\circ}C$

4. Pulse test: $PW \le 300\mu s$, duty cycle $\le 2\%$.

5. For DESIGN AID ONLY, not subject to production testing.

6. Switching time is essentially independent of operating temperature.

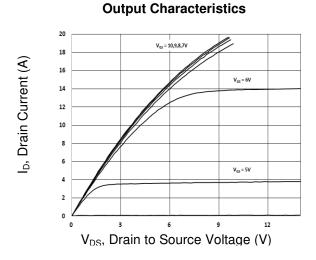
ORDERING INFORMATION

PART NO.	PACKAGE	PACKING
TSM60NB380CP ROG	TO-252 (DPAK)	2,500pcs / 13" Reel



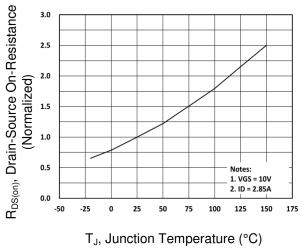
CHARACTERISTICS CURVES

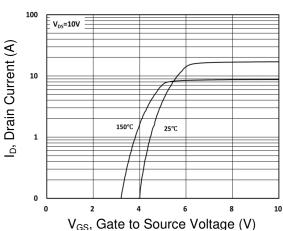
 $(T_c = 25^{\circ}C \text{ unless otherwise noted})$



On-Resistance vs. Drain Current $R_{DS(on)}$, Drain-Source On-Resistance (Ω) 0.55 0.50 0.45 0.40 V_{GS} = 10V 0.35 V_{G5} = 20V 0.30 0.25 *Note: T_c = 25°C 0.20 5 15 0 10 20 25 30 I_D, Drain Current (A)

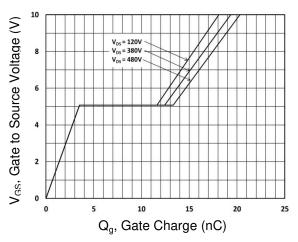
On-Resistance vs. Junction Temperature



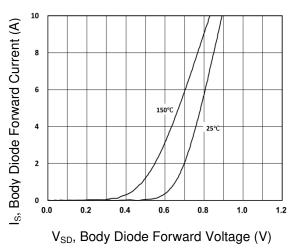


Transfer Characteristics

Gate-Source Voltage vs. Gate Charge



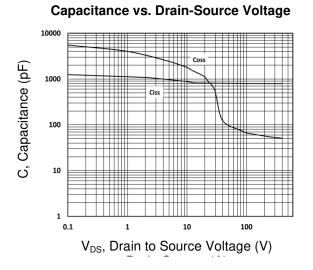
Source-Drain Diode Forward Current vs. Voltage



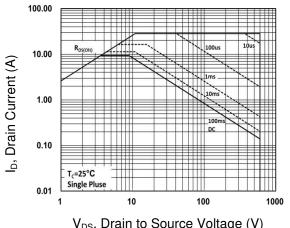


CHARACTERISTICS CURVES

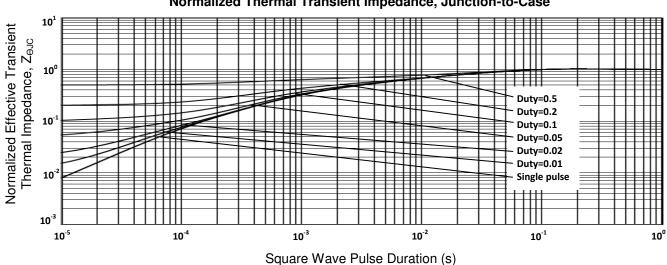
 $(T_c = 25^{\circ}C \text{ unless otherwise noted})$



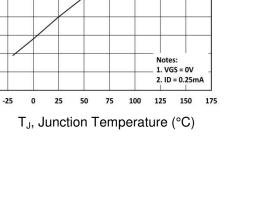
Maximum Safe Operating Area



V_{DS}, Drain to Source Voltage (V)



Normalized Thermal Transient Impedance, Junction-to-Case



BV_{DSS} vs. Junction Temperature

1.15

1.10

1.05

1.00

0.95

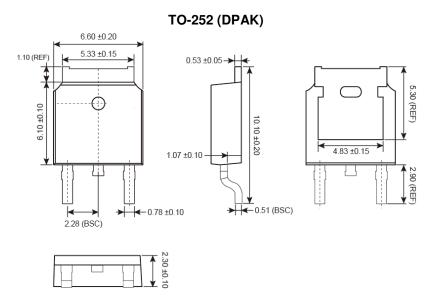
0.90

-50

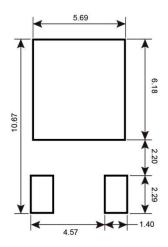
BV_{DSS} (Normalized) Drain-Source Breakdown Voltage



PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)



SUGGESTED PAD LAYOUT (Unit: Millimeters)



MARKING DIAGRAM

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	60 YLN	NB3 VI	80	
#	7, 1	U	{}	8

Υ	= Year Code			
Μ	= Month Code	9		
	O =Jan	P =Feb	Q =Mar	R =Apr
	S =May	T =Jun	U =Jul	V =Aug
	W =Sep	X =Oct	Y =Nov	Z =Dec
L	= Lot Code (1	~9, A~Z)		



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